
Oral presentation | 13 Semiconductors | 13.7 Compound and power electron devices and process technology

[20a-E301-1~12]13.7 Compound and power electron devices and process technology

Kenji Shiojima(Univ. of Fukui)

Fri. Sep 20, 2019 9:00 AM - 12:15 PM E301 (E301)

△ : Presentation by Applicant for JSAP Young Scientists Presentation Award

▲ : English Presentation

▼ : Both of Above

No Mark : None of Above

9:00 AM - 9:15 AM

[20a-E301-1][INVITED] Temperature dependence of barrier height in Ni/n-GaN Schottky barrier diode

OTakuya Maeda¹, Masaya Okada², Masaki Ueno², Yoshiyuki Yamamoto², Tsunenobu Kimoto¹, Masahiro Horita³, Jun Suda³ (1.Kyoto Univ., 2.Sumitomo Electric Industries, 3.Nagoya Univ.)

Keywords:JSAP Paper Award